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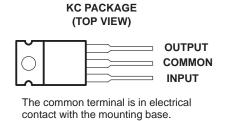
±1% Output Tolerance at 25°C

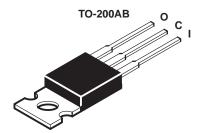
**Thermal Shutdown** 

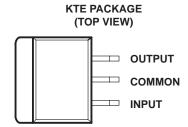
- ±2% Output Tolerance Over Full Operating Range
- Internal Short-Circuit Current Limiting
- Pinout Identical to µA7800 Series
- Improved Version of μA7800 Series

### description

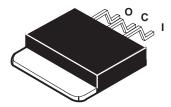
Each fixed-voltage precision regulator in this series is capable of supplying 1.5 A of load current. A unique temperature-compensation technique coupled with an internally trimmed band-gap reference has resulted in improved accuracy when compared to other 3-terminal regulators. Advanced layout techniques provide excellent line, load, and thermal regulation. The internal current limiting and thermal shutdown features make the devices essentially immune to overload.







The common terminal is in electrical contact with the mounting base.



#### **AVAILABLE OPTIONS**

		PACKAGEI	DEVICES	CHIP	
Тј	(V) HEAT-SINK MOUNTED (V) (KC)		PLASTIC FLANGE MOUNTED (KTE)†	FORM (Y)	
	5	TL78005CKC	TL78005CKTE	TL78005Y	
0°C to 125°C	12	TL78012CKC	TL78012CKTE	TL78012Y	
	15	TL78015CKC	TL78015CKTE	TL78015Y	

<sup>†</sup> The KTE package is also available taped and reeled.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

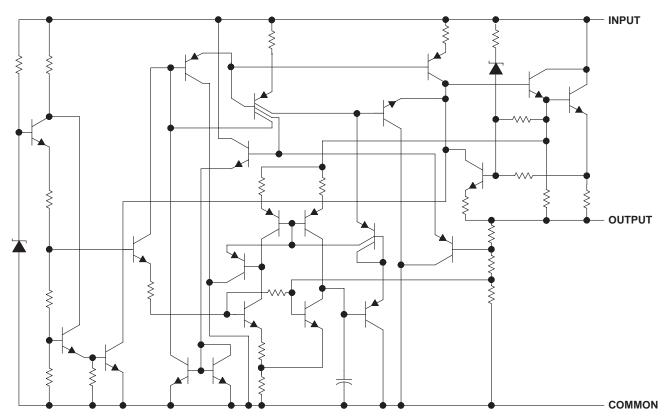
PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



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#### schematic

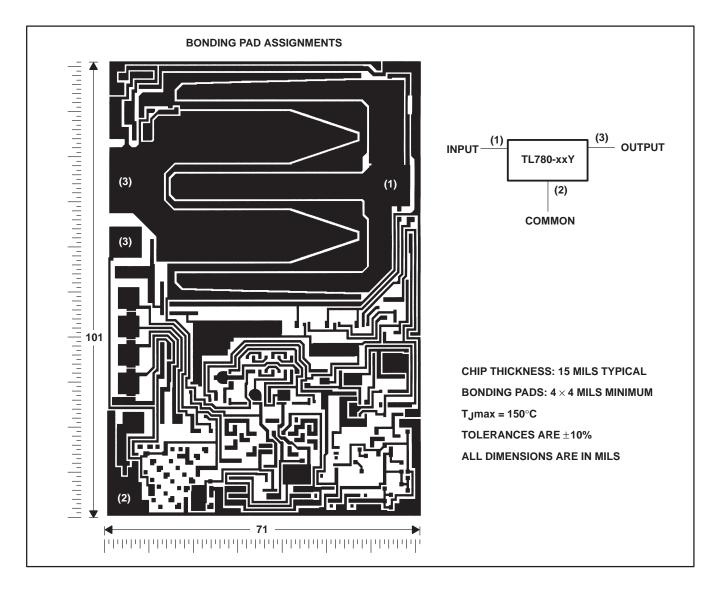




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#### TL780-05Y, TL780-12Y, and TL780-15Y chip information

These chips, when properly assembled, display characteristics similar to the TL780-xxC Series. Thermal compression or ultrasonic bonding may be used on the doped aluminum bonding pads. The chips may be mounted with conductive epoxy or a gold-silicon preform.





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#### absolute maximum ratings over operating temperature range (unless otherwise noted)<sup>†</sup>

Input voltage, V <sub>I</sub>
Continuous total power dissipation at $T_A = 25^{\circ}C$ (see Note 1)
Continuous total power dissipation at (or below) $T_C = 25^{\circ}C$ (see Note 1) See Dissipation Rating Tables
Operating free-air, T <sub>A</sub> , case, T <sub>C</sub> , or virtual junction, T <sub>J</sub> , temperature range
Storage temperature range, T <sub>stg</sub> 65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds

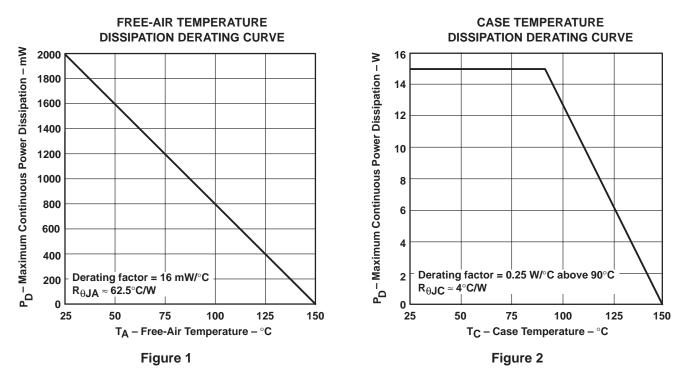
<sup>+</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: For operation above  $T_A = 25^{\circ}C$  or  $T_C = 25^{\circ}C$ , refer to Figure 1 and Figure 2. To avoid exceeding the design maximum virtual junction temperature, these ratings should not be exceeded. Due to variations in individual device electrical characteristics and thermal resistance, the built-in thermal overload protection may be activated at power levels slightly above or below the rated dissipation.

PACKAGE	T <sub>A</sub> ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 70°C POWER RATING	T <sub>A</sub> = 105°C POWER RATING	T <sub>A</sub> = 125°C POWER RATING
KC	2000 mW	16.0 mW/°C	1280 mW	720 mW	400 mW
KTE	1900 mW	15.2 mW/°C	1216 mW	684 mW	380 mW

#### DISSIPATION RATING TABLE - CASE TEMPERATURE

PACKAGE	T <sub>C</sub> ≤ 90°C POWER RATING	DERATING FACTOR ABOVE T <sub>C</sub> = 90°C	T <sub>A</sub> = 125°C POWER RATING
KC	15000 mW	250.0 mW/°C	6250 mW
KTE	14300 mW	238.0 mW/°C	5970 mW





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#### recommended operating conditions

		MIN	MAX	UNIT
Input voltage, V <sub>I</sub>	TL780-05C	7	25	
	TL780-12C	14.5	30	V
	TL780-15C	17.5	30	
Output current, IO			1.5	A
Operating virtual junction temperature, TJ		0	125	°C

# electrical characteristics at specified virtual junction temperature, $V_I = 10 V$ , $I_O = 500 mA$ (unless otherwise noted)

	TEAT CONDITIONS	- +	TL	780-050	;	UNIT
PARAMETER	TEST CONDITIONS	T <sub>J</sub> †	MIN	TYP	MAX	
Output veltage	$I_{O} = 5 \text{ mA to 1 A}, \qquad P \le 15 \text{ W},$	25°C	4.95	5	5.05	V
Output voltage	$V_{I} = 7 V \text{ to } 20 V$	0°C to 125°C	4.9		5.1	v
	$V_{I} = 7 V \text{ to } 25 V$	25°C		0.5	5	
Input voltage regulation	V <sub>I</sub> = 8 V to 12 V			0.5	5	mV
Ripple rejection	V <sub>I</sub> = 8 V to 18 V, f = 120 Hz	0°C to 125°C	70	85		dB
Output voltage regulation	IO = 5 mA to 1.5 A	0500		4	25	mV
	I <sub>O</sub> = 250 mA to 750 mA	25°C		1.5	15	
Output resistance	f = 1 kHz	0°C to 125°C	(	0.0035		Ω
Temperature coefficient of output voltage	IO = 5 mA	0°C to 125°C		0.25		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	25°C		75		μV
Dropout voltage	I <sub>O</sub> = 1 A	25°C		2		V
Input bias current		25°C		5	8	mA
	V <sub>I</sub> = 7 V to 25 V	000 to 40500		0.7	1.3	
Input bias current change	$I_{O} = 5 \text{ mA to 1 A}$	0°C to 125°C		0.003	0.5	mA
Short-circuit output current		25°C		750		mA
Peak output current		25°C		2.2		А

<sup>†</sup> Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.22-μF capacitor across the output.



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# electrical characteristics at specified virtual junction temperature, $V_I = 19 V$ , $I_O = 500 mA$ (unless otherwise noted)

DADAMETER		<b>+</b> +	TL780-12	С	UNIT
PARAMETER	TEST CONDITIONS	TJ <sup>†</sup>	MIN TYP	MAX	
Output up the pre	$I_{O} = 5 \text{ mA to 1 A}, \qquad P \le 15 \text{ W},$	25°C	11.88 12	12.12	v
Output voltage	$V_{I} = 14.5 V \text{ to } 27 V$	0°C to 125°C	11.76	12.24	1 <sup>×</sup>
	V <sub>I</sub> = 14.5 V to 30 V	0500	1.2	12	
Input voltage regulation	$V_{I} = 16 V \text{ to } 22 V$	25°C	1.2	12	mV
Ripple rejection	V <sub>I</sub> = 15 V to 25 V, f = 120 Hz	0°C to 125°C	65 80		dB
Output voltage regulation	IO = 5 mA to 1.5 A	0500	6.5	60	
	I <sub>O</sub> = 250 mA to 750 mA	25°C	2.5		- mV
Output resistance	f = 1 kHz	0°C to 125°C	0.0035		Ω
Temperature coefficient of output voltage	IO = 5 mA	0°C to 125°C	0.6		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	25°C	180		μV
Dropout voltage	I <sub>O</sub> = 1 A	25°C	2		V
Input bias current		25°C	5.5	8	mA
have at the second set of a second	V <sub>I</sub> = 14.5 V to 30 V	000 1- 40500	0.4	1.3	
Input bias current change	$I_{O} = 5 \text{ mA to } 1 \text{ A}$	0°C to 125°C	0.03	0.5	mA
Short-circuit output current		25°C	350		mA
Peak output current		25°C	2.2	-	A

<sup>†</sup> Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.22-μF capacitor across the output.

# electrical characteristics at specified virtual junction temperature, $V_I = 23 V$ , $I_O = 500 mA$ (unless otherwise noted)

DADAMETED	TEST CONDITIONS	<b>T</b> . <b>†</b>	TL780	)-15C	LINUT
PARAMETER	TEST CONDITIONS	TJ <sup>†</sup>	MIN T	YP M/	
Outrast units as	$I_{O} = 5 \text{ mA to 1 A}, \qquad P \le 15 \text{ W},$	25°C	14.85	15 15.	15 V
Output voltage	VI = 17.5 V to 30 V	0°C to 125°C	14.7	15	.3 V
	V <sub>I</sub> = 17.5 V to 30 V	0500		1.5	15
nput voltage regulation	V <sub>I</sub> = 20 V to 26 V	25°C		1.5	15 mV
Ripple rejection	V <sub>I</sub> = 18.5 V to 28.5 V, f = 120 Hz	0°C to 125°C	60	75	dB
Output voltage regulation	I <sub>O</sub> = 5 mA to 1.5 A			7	75
	I <sub>O</sub> = 250 mA to 750 mA	25°C		2.5	45 mV
Output resistance	f = 1 kHz	1	0.0	035	Ω
Temperature coefficient of output voltage	I <sub>O</sub> = 5 mA	0°C to 125°C	0	.62	mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	25°C	:	225	μV
Dropout voltage	I <sub>O</sub> = 1 A	25°C		2	V
Input bias current		25°C		5.5	8 mA
lanut bing gument abagan	V <sub>I</sub> = 17.5 V to 30 V	000 to 40500		0.4 1	.3
Input bias current change	$I_{O} = 5 \text{ mA to 1 A}$	0°C to 125°C	0	.02 (	.5 mA
Short-circuit output current		25°C		230	mA
Peak output current		25°C		2.2	A

<sup>†</sup> Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.22-μF capacitor across the output.



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### electrical characteristics, $V_I = 10 V$ , $I_O = 500 mA$ , $T_J = 25^{\circ}C$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS <sup>†</sup>	TL	TL780-05Y		
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Output voltage	$I_{O} = 5 \text{ mA to 1 A}, \qquad P \le 15 \text{ W},$		5		V
loguit veltege regulation	$V_{I} = 7 V \text{ to } 25 V$	0.5		mV	
nput voltage regulation	$V_{I} = 8 V$ to 12 V		0.5		mv
	$I_{O} = 5 \text{ mA to } 1.5 \text{ A}$	4			
Output voltage regulation	$I_{O} = 250 \text{ mA to } 750 \text{ mA}$		1.5		mV
Output noise voltage	f = 10 Hz to 100 kHz		75		μV
Dropout voltage	I <sub>O</sub> = 1 A		2		V
Input bias current			5		mA
Short-circuit output current			750		mA
Peak output current			2.2		А

<sup>†</sup> Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.22-μF capacitor across the output.

### electrical characteristics, $V_I = 19 V$ , $I_O = 500 mA$ , $T_J = 25^{\circ}C$ (unless otherwise noted)

PARAMETER	TENT CONDITIONOT	TL780-12Y	UNIT
PARAMETER	TEST CONDITIONS <sup>†</sup>	MIN TYP MAX	UNIT
Output voltage	$I_{O} = 5 \text{ mA to 1 A}, \qquad P \le 15 \text{ W},$	12	V
	V <sub>I</sub> = 14.5 V to 30 V	1.2	mV
Input voltage regulation	V <sub>I</sub> = 16 V to 22 V	1.2	mv
	I <sub>O</sub> = 5 mA to 1.5 A	6.5	mV
Output voltage regulation	I <sub>O</sub> = 250 mA to 750 mA	2.5	IIIV
Output noise voltage	f = 10 Hz to 100 kHz	180	μV
Dropout voltage	I <sub>O</sub> = 1 A	2	V
Input bias current		5.5	mA
Short-circuit output current		350	mA
Peak output current		2.2	А

<sup>†</sup> Pulse-testing techniques the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.22-μF capacitor across the output.

## electrical characteristics, V<sub>I</sub> = 23 V, I<sub>O</sub> = 500 mA, T<sub>J</sub> = 25 $^{\circ}$ C (unless otherwise noted)

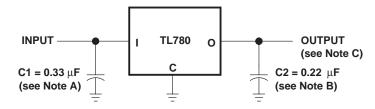
	TEST CONDITIONS <sup>†</sup>	TL780-15Y	LINUT
PARAMETER	TEST CONDITIONST	MIN TYP MAX	UNIT
Output voltage	$I_{O} = 5 \text{ mA to 1 A}, \qquad P \le 15 \text{ W},$	15	V
	V <sub>I</sub> = 17.5 V to 30 V	1.5	
Input voltage regulation	$V_{I} = 20 V$ to 26 V	1.5	mV
	$I_{O} = 5 \text{ mA to } 1.5 \text{ A}$	7	mV
Output voltage regulation	I <sub>O</sub> = 250 mA to 750 mA	2.5	mv
Output resistance	f = 1 kHz	0.0035	Ω
Output noise voltage	f = 10 Hz to 100 kHz	225	μV
Dropout voltage	I <sub>O</sub> = 1 A	2	V
Input bias current		5.5	mA
Short-circuit output current		230	mA
Peak output current		2.2	А

<sup>†</sup> Pulse-testing techniques the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.22-μF capacitor across the output.



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#### PARAMETER MEASUREMENT INFORMATION



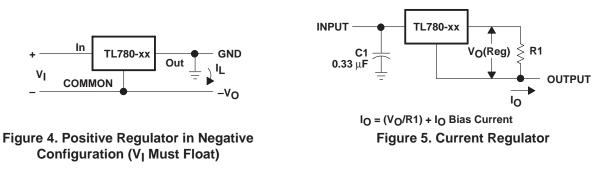
- NOTES: A. C1 is required when the regulator is far from the power supply filter.
  - B. C2 is not required for stability; however, transient response is improved.
  - C. Permanent damage can occur when output is pulled below ground.

Figure 3. Test Circuit



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### **APPLICATION INFORMATION**



#### operation with a load common to a voltage of opposite polarity

In many cases, a regulator powers a load that is not connected to ground but instead is connected to a voltage source of opposite polarity (e.g., operational amplifiers, level-shifting circuits, etc.). In these cases, a clamp diode should be connected to the regulator output as shown in Figure 6. This protects the regulator from output polarity reversals during startup and short-circuit operation.

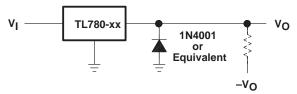


Figure 6. Output Polarity Reversal Protection Circuit

#### reverse-bias protection

Occasionally, the input voltage to the regulator can collapse faster than the output voltage. This, for example, could occur when the input supply is crowbarred during an output overvoltage condition. If the output voltage is greater than approximately 7 V, the emitter-base junction of the series pass element (internal or external) could break down and be damaged. To prevent this, a diode shunt can be employed, as shown in Figure 7.

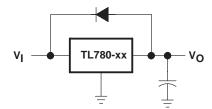


Figure 7. Reverse-Bias Protection Circuit

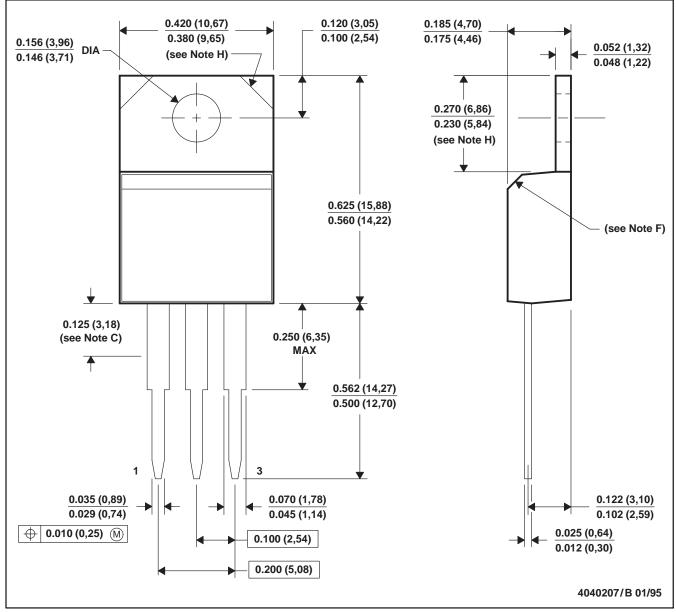


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KC (R-PSFM-T3)

MECHANICAL INFORMATION

PLASTIC FLANGE-MOUNT PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. Lead dimensions are not controlled within this area.
- D. All lead dimensions apply before solder dip.
- E. The center lead is in electrical contact with the mounting tab.
- F. The chamfer is optional.
- G. Falls within JEDEC TO-220AB
- H. Tab contour optional within these dimensions

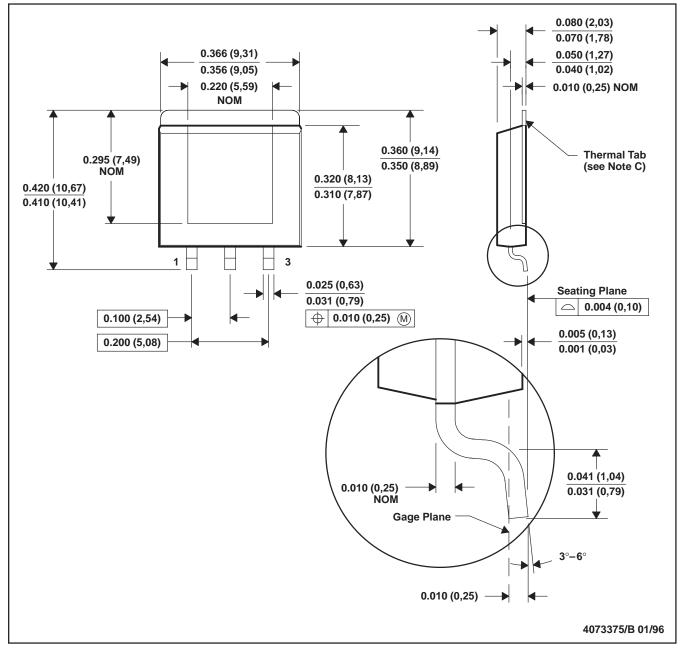


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MECHANICAL INFORMATION



#### PLASTIC FLANGE-MOUNT PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. The center lead is in electrical contact with the thermal tab.



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